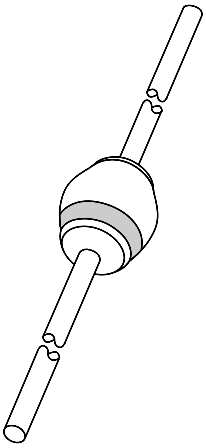
DATA SHEET



BYM36 series
Fast soft-recovery controlled avalanche rectifiers

Product specification
Supersedes data of 1996 May 30

1996 Sep 18

Philips Semiconductors

PHILIPS

Fast soft-recovery controlled avalanche rectifiers

BYM36 series

FEATURES

- Glass passivated
- High maximum operating temperature
- Low leakage current
- Excellent stability
- Guaranteed avalanche energy absorption capability
- Available in ammo-pack
- Also available with preformed leads for easy insertion.

DESCRIPTION

Rugged glass SOD64 package, using a high temperature alloyed construction.

This package is hermetically sealed and fatigue free as coefficients of expansion of all used parts are matched.

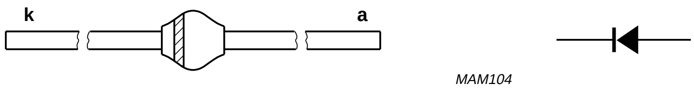


Fig.1 Simplified outline (SOD64) and symbol.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{RRM}	repetitive peak reverse voltage				
	BYM36A		–	200	V
	BYM36B		–	400	V
	BYM36C		–	600	V
	BYM36D		–	800	V
	BYM36E		–	1000	V
	BYM36F		–	1200	V
	BYM36G		–	1400	V
V_R	continuous reverse voltage				
	BYM36A		–	200	V
	BYM36B		–	400	V
	BYM36C		–	600	V
	BYM36D		–	800	V
	BYM36E		–	1000	V
	BYM36F		–	1200	V
	BYM36G		–	1400	V
$I_{F(AV)}$	average forward current	T_{tp} = 55 °C; lead length = 10 mm; see Figs 2; 3 and 4 averaged over any 20 ms period; see also Figs 14; 15 and 16			
	BYM36A to C		–	3.0	A
	BYM36D and E		–	2.9	A
	BYM36F and G		–	2.9	A
$I_{F(AV)}$	average forward current	T_{amb} = 65 °C; PCB mounting (see Fig.25); see Figs 5; 6 and 7 averaged over any 20 ms period; see also Figs 14; 15 and 16			
	BYM36A to C		–	1.25	A
	BYM36D and E		–	1.20	A
	BYM36F and G		–	1.15	A

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{FRM}	repetitive peak forward current	T_{tp} = 55 °C; see Figs 8; 9 and 10			
	BYM36A to C		–	37	A
	BYM36D and E		–	33	A
	BYM36F and G		–	27	A
I_{FRM}	repetitive peak forward current	T_{amb} = 65 °C; see Figs 11; 12 and 13			
	BYM36A to C		–	13	A
	BYM36D and E		–	11	A
	BYM36F and G		–	10	A
I_{FSM}	non-repetitive peak forward current	t = 10 ms half sine wave; $T_j = T_{j\,max}$ prior to surge; $V_R = V_{RRMmax}$	–	65	A
E_{RSM}	non-repetitive peak reverse avalanche energy	L = 120 mH; $T_j = T_{j\,max}$ prior to surge; inductive load switched off	–	10	mJ
T_{stg}	storage temperature		–65	+175	°C
T_j	junction temperature	see Figs 17 and 18	–65	+175	°C

ELECTRICAL CHARACTERISTICS

T_j = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_F	forward voltage	I_F = 3 A; $T_j = T_{j\,max}$; see Figs 19; 20 and 21				
	BYM36A to C		–	–	1.22	V
	BYM36D and E		–	–	1.28	V
	BYM36F and G		–	–	1.24	V
V_F	forward voltage	I_F = 3 A; see Figs 19; 20 and 21				
	BYM36A to C		–	–	1.60	V
	BYM36D and E		–	–	1.78	V
	BYM36F and G		–	–	1.57	V
$V_{(BR)R}$	reverse avalanche breakdown voltage	I_R = 0.1 mA				
	BYM36A		300	–	–	V
	BYM36B		500	–	–	V
	BYM36C		700	–	–	V
	BYM36D		900	–	–	V
	BYM36E		1100	–	–	V
	BYM36F		1300	–	–	V
	BYM36G		1500	–	–	V
I_R	reverse current	$V_R = V_{RRMmax}$; see Fig.22	–	–	5	µA
		$V_R = V_{RRMmax}$; T_j = 165 °C; see Fig.22	–	–	150	µA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
t_{rr}	reverse recovery time	when switched from I_F = 0.5 A to I_R = 1 A; measured at I_R = 0.25 A; see Fig. 26				
	BYM36A to C		–	–	100	ns
	BYM36D and E		–	–	150	ns
	BYM36F and G		–	–	250	ns
C_d	diode capacitance	f = 1 MHz; V_R = 0 V; see Figs 23 and 24				
	BYM36A to C		–	85	–	pF
	BYM36D and E		–	75	–	pF
	BYM36F and G		–	65	–	pF
$\left\lvert\frac{dI_R}{dt}\right\rvert$	maximum slope of reverse recovery current	when switched from I_F = 1 A to $V_R \geq$ 30 V and dI_F/dt = –1 A/µs; see Fig.27				
	BYM36A to C		–	–	7	A/µs
	BYM36D and E		–	–	6	A/µs
	BYM36F and G		–	–	5	A/µs

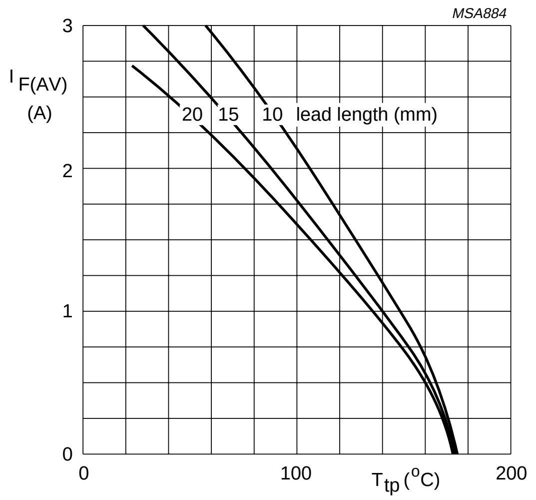
THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j\text{-}tp}$	thermal resistance from junction to tie-point	lead length = 10 mm	25	K/W
$R_{th\ j\text{-}a}$	thermal resistance from junction to ambient	note 1	75	K/W

Note

1. Device mounted on an epoxy-glass printed-circuit board, 1.5 mm thick; thickness of Cu-layer ≥40 µm, see Fig.25. For more information please refer to the *"General Part of associated Handbook"*.

GRAPHICAL DATA

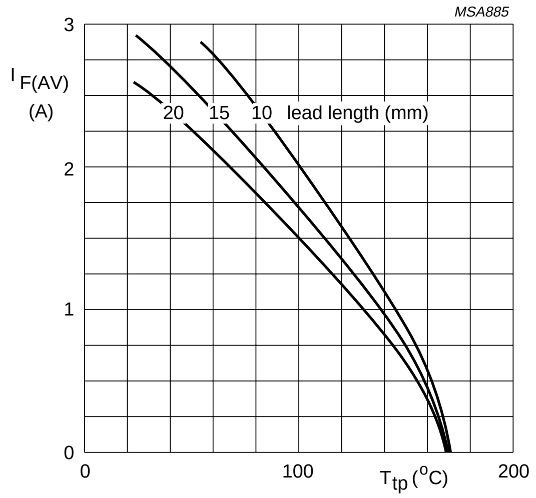


BYM36A to C

a = 1.42; $V_R = V_{RRMmax}$; δ = 0.5.

Switched mode application.

Fig.2 Maximum average forward current as a function of tie-point temperature (including losses due to reverse leakage).

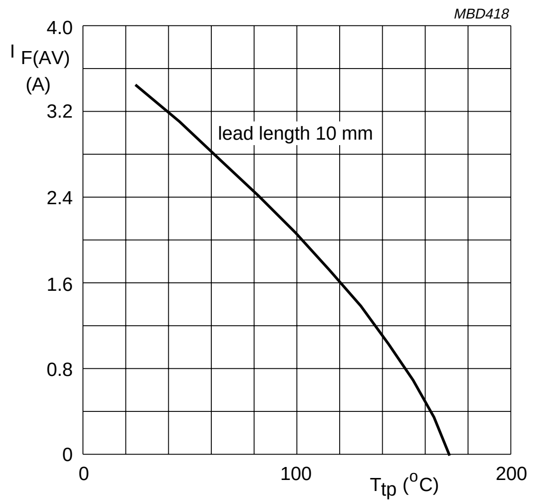


BYM36D and E

a = 1.42; $V_R = V_{RRMmax}$; δ = 0.5.

Switched mode application.

Fig.3 Maximum average forward current as a function of tie-point temperature (including losses due to reverse leakage).

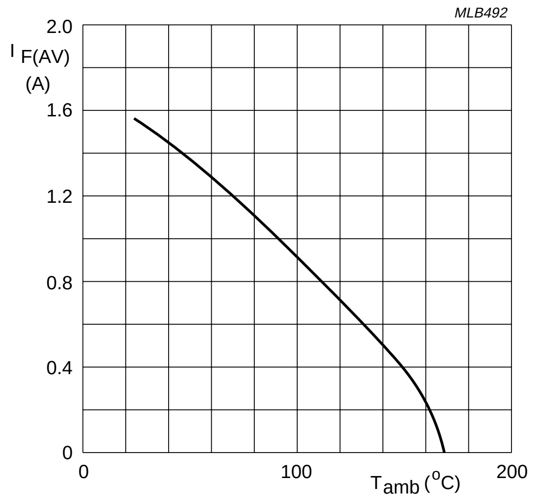


BYM36F and G

a = 1.42; $V_R = V_{RRMmax}$; δ = 0.5.

Switched mode application.

Fig.4 Maximum average forward current as a function of tie-point temperature (including losses due to reverse leakage).



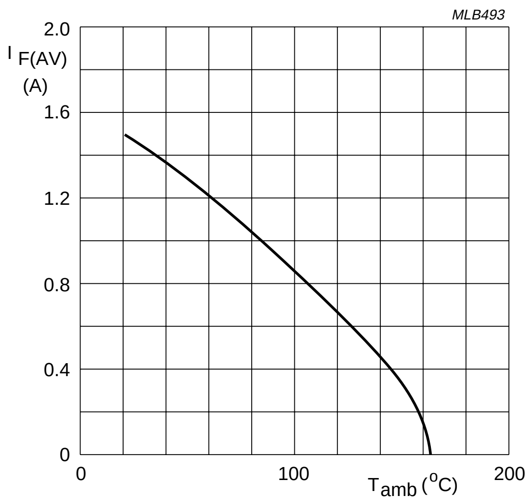
BYM36A to C

a = 1.42; $V_R = V_{RRMmax}$; δ = 0.5.

Device mounted as shown in Fig.25.

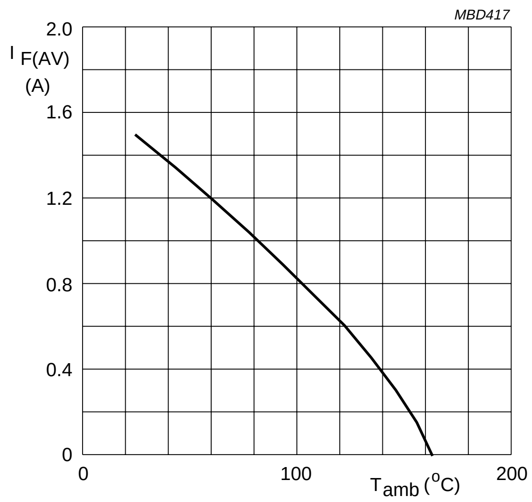
Switched mode application.

Fig.5 Maximum average forward current as a function of ambient temperature (including losses due to reverse leakage).



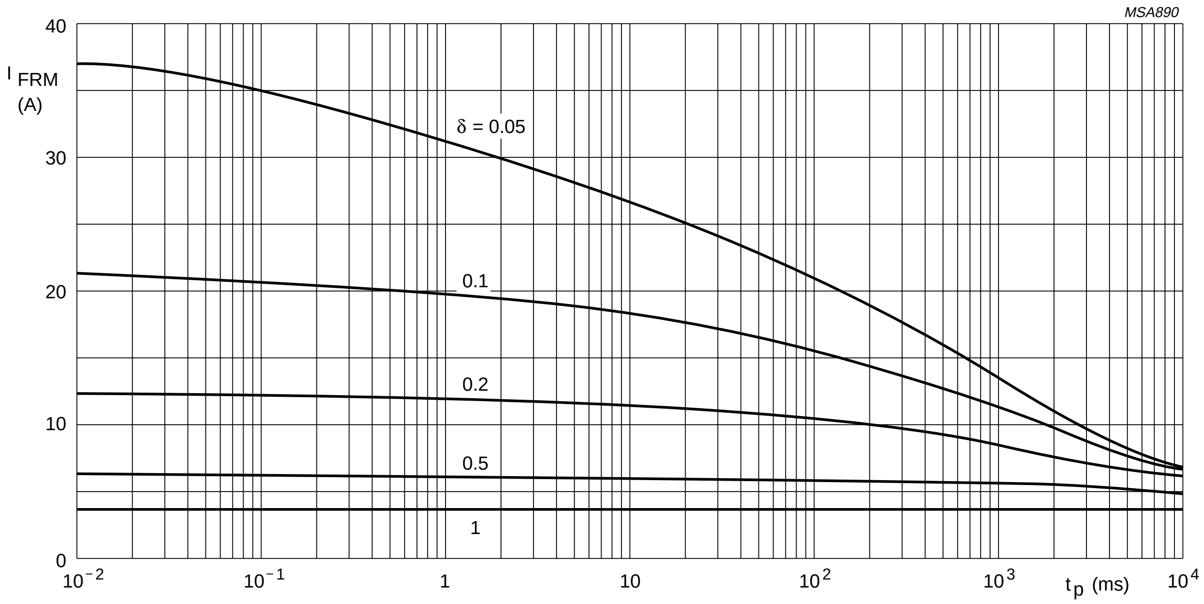
BYM36D and E
a = 1.42; $V_R = V_{RRMmax}$; δ = 0.5.
Device mounted as shown in Fig.25.
Switched mode application.

Fig.6 Maximum average forward current as a function of ambient temperature (including losses due to reverse leakage).



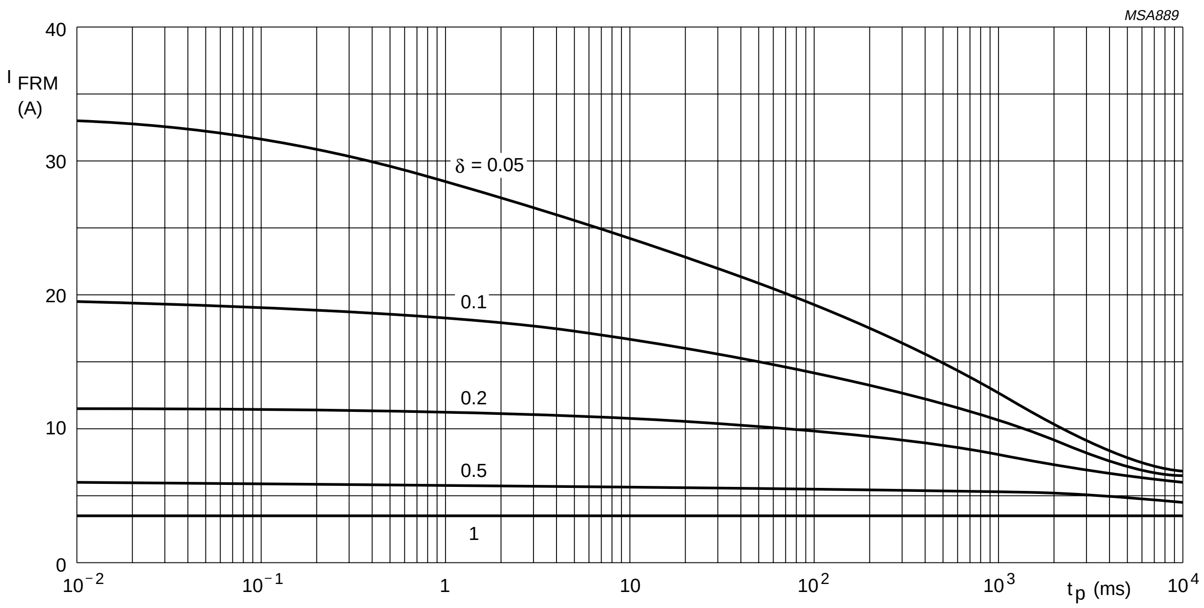
BYM36F and G
a = 1.42; $V_R = V_{RRMmax}$; δ = 0.5.
Device mounted as shown in Fig.25.
Switched mode application.

Fig.7 Maximum average forward current as a function of ambient temperature (including losses due to reverse leakage).



BYM36A to C
T_{tp} = 55°C; $R_{th\ j\text{-}tp}$ = 25 K/W.
V_{RRMmax} during 1 – δ; curves include derating for $T_{j\ max}$ at V_{RRM} = 600 V.

Fig.8 Maximum repetitive peak forward current as a function of pulse time (square pulse) and duty factor.

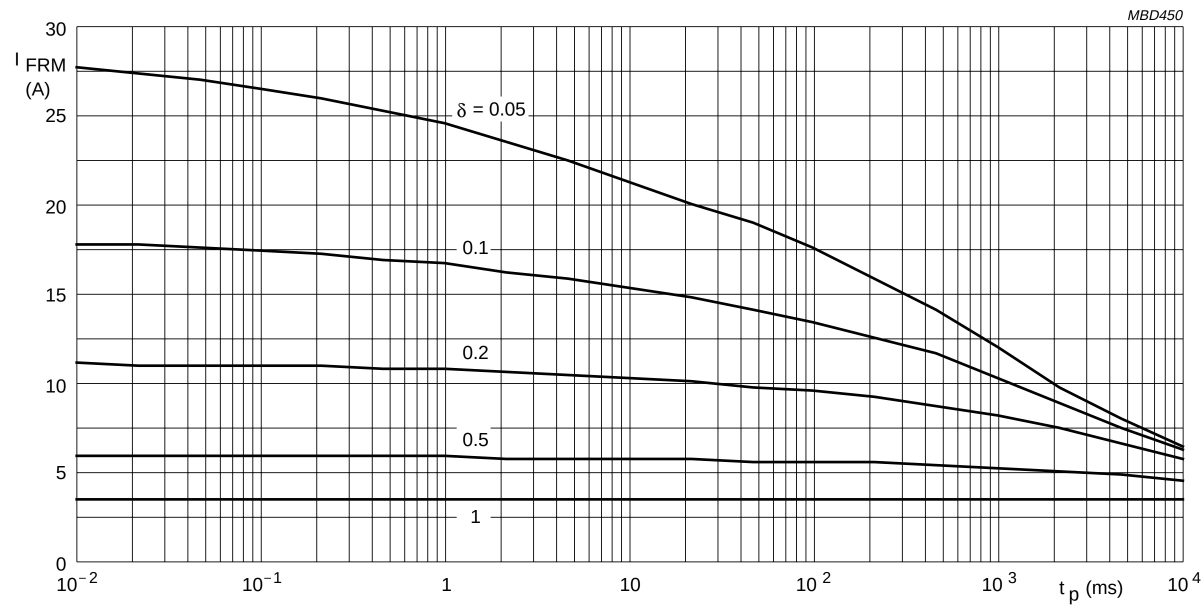


BYM36D and E

T_{tp} = 55°C; $R_{th\ j\text{-}tp}$ = 25 K/W.

V_{RRMmax} during 1 – δ; curves include derating for $T_{j\ max}$ at V_{RRM} = 1000 V.

Fig.9 Maximum repetitive peak forward current as a function of pulse time (square pulse) and duty factor.

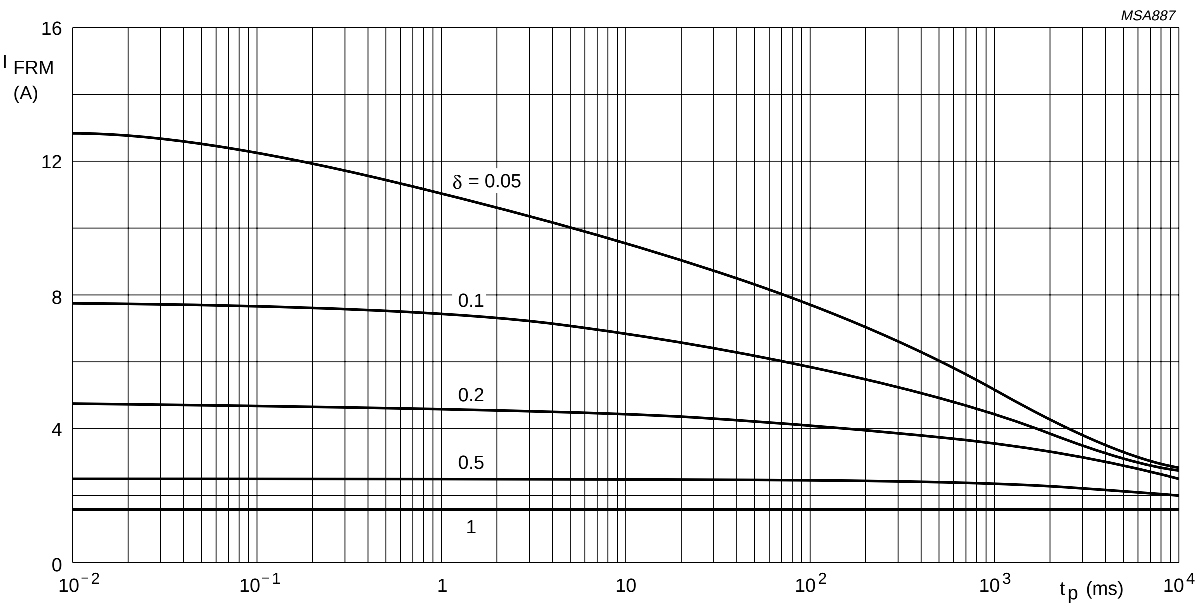


BYM36F and G

T_{tp} = 55°C; $R_{th\ j\text{-}tp}$ = 25 K/W.

V_{RRMmax} during 1 – δ; curves include derating for $T_{j\ max}$ at V_{RRM} = 1400 V.

Fig.10 Maximum repetitive peak forward current as a function of pulse time (square pulse) and duty factor.

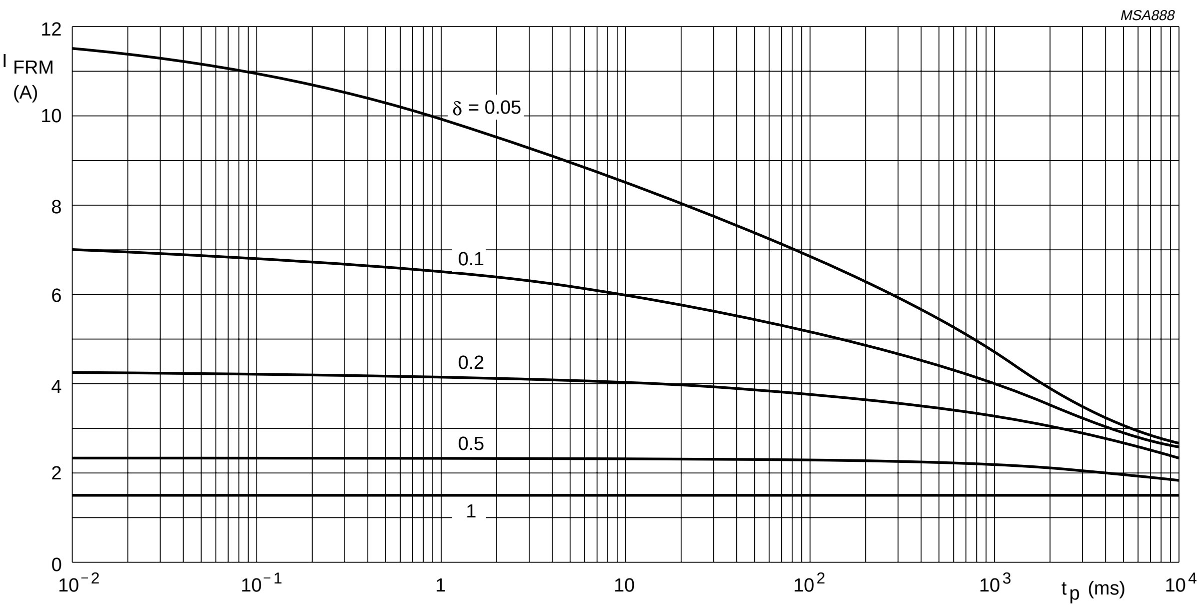


BYM36A to C

T_{amb} = 65 °C; $R_{th\ j\text{-}a}$ = 75 K/W.

V_{RRMmax} during 1 – δ; curves include derating for $T_{j\ max}$ at V_{RRM} = 600 V.

Fig.11 Maximum repetitive peak forward current as a function of pulse time (square pulse) and duty factor.

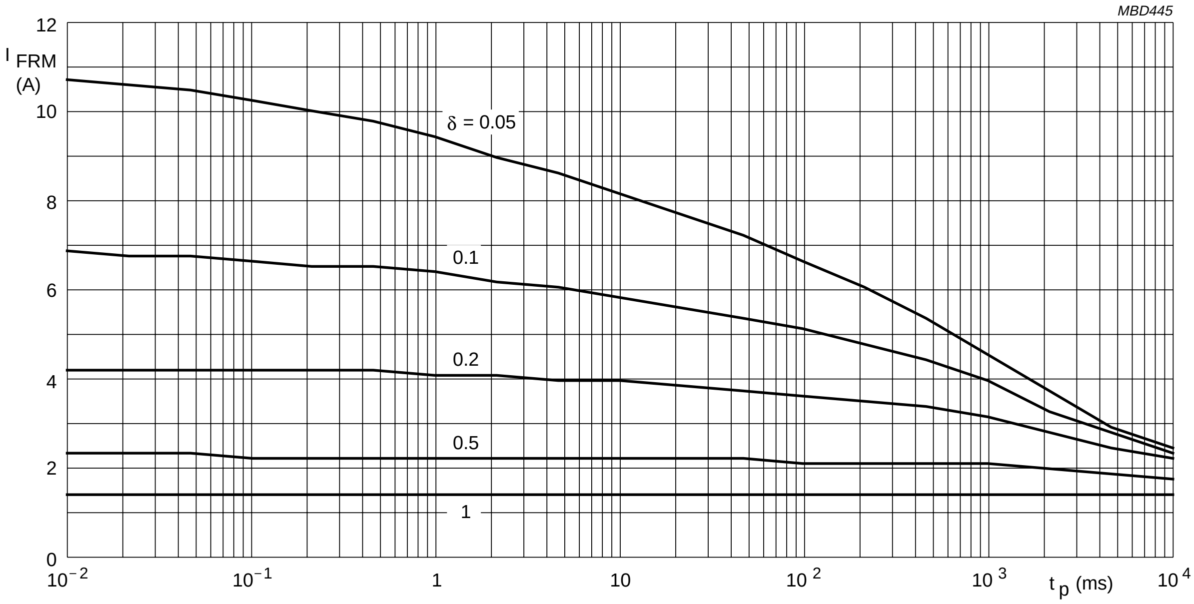


BYM36D and E

T_{amb} = 65 °C; $R_{th\ j\text{-}a}$ = 75 K/W.

V_{RRMmax} during 1 – δ; curves include derating for $T_{j\ max}$ at V_{RRM} = 1000 V.

Fig.12 Maximum repetitive peak forward current as a function of pulse time (square pulse) and duty factor.

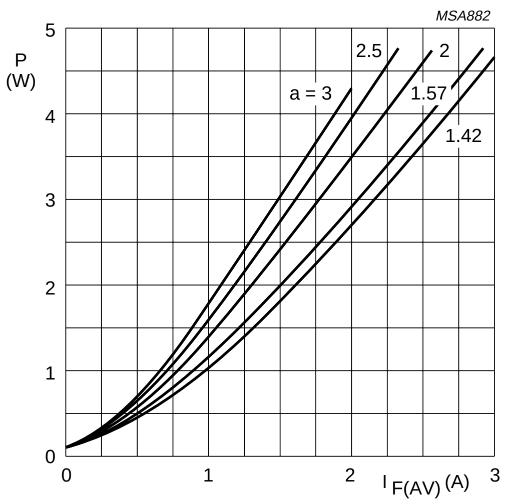


BYM36F and G

T_{amb} = 65 °C; $R_{th\ j-a}$ = 75 K/W.

V_{RRMmax} during 1 – δ; curves include derating for $T_{j\ max}$ at V_{RRM} = 1400 V.

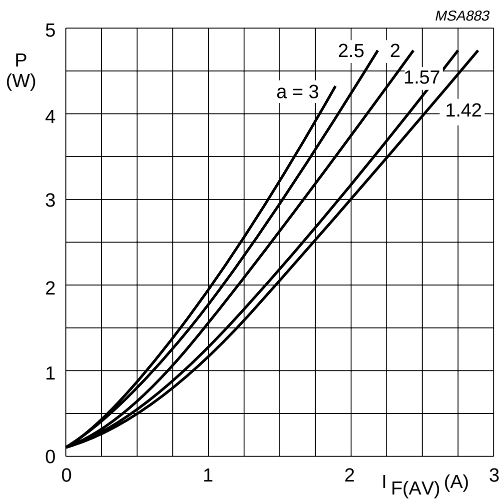
Fig.13 Maximum repetitive peak forward current as a function of pulse time (square pulse) and duty factor.



BYM36A to C

a = $I_{F(RMS)}/I_{F(AV)}$; $V_R = V_{RRMmax}$; δ = 0.5.

Fig.14 Maximum steady state power dissipation (forward plus leakage current losses, excluding switching losses) as a function of average forward current.



BYM36D and E

a = $I_{F(RMS)}/I_{F(AV)}$; $V_R = V_{RRMmax}$; δ = 0.5.

Fig.15 Maximum steady state power dissipation (forward plus leakage current losses, excluding switching losses) as a function of average forward current.

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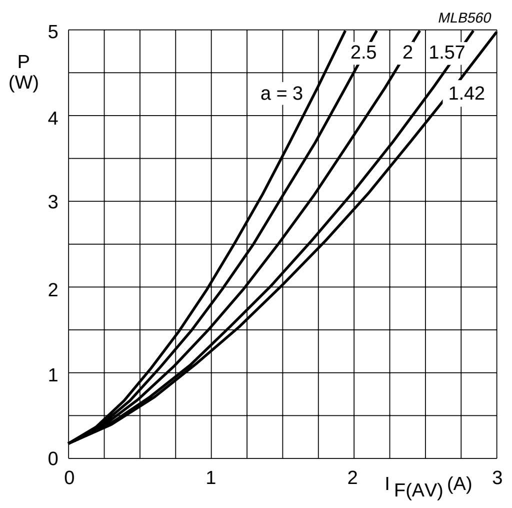
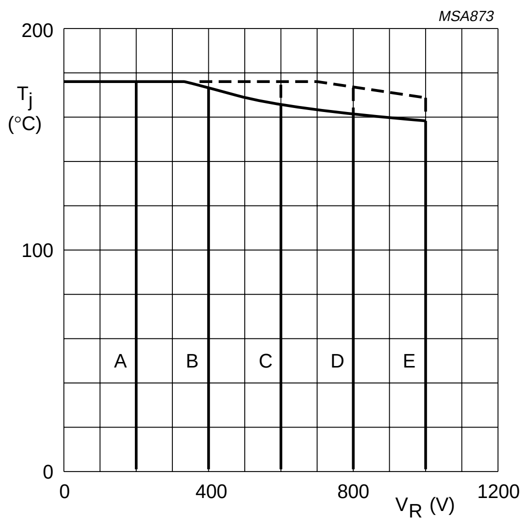


BYM36F and G

a = $I_{F(RMS)}/I_{F(AV)}$; $V_R = V_{RRMmax}$; $\delta = 0.5$.

Fig.16 Maximum steady state power dissipation (forward plus leakage current losses, excluding switching losses) as a function of average forward current.

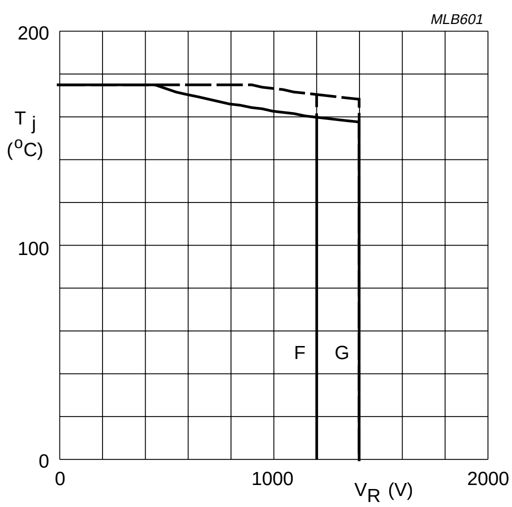


BYM36A to E

Solid line = V_R.

Dotted line = V_{RRM}; $\delta = 0.5$.

Fig.17 Maximum permissible junction temperature as a function of reverse voltage.

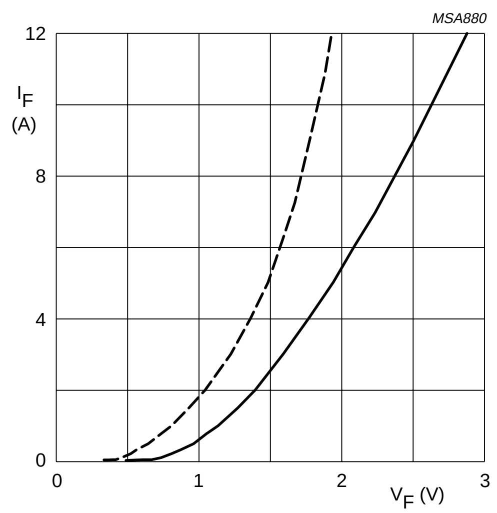


BYM36F and G

Solid line = V_R.

Dotted line = V_{RRM}; $\delta = 0.5$.

Fig.18 Maximum permissible junction temperature as a function of reverse voltage.

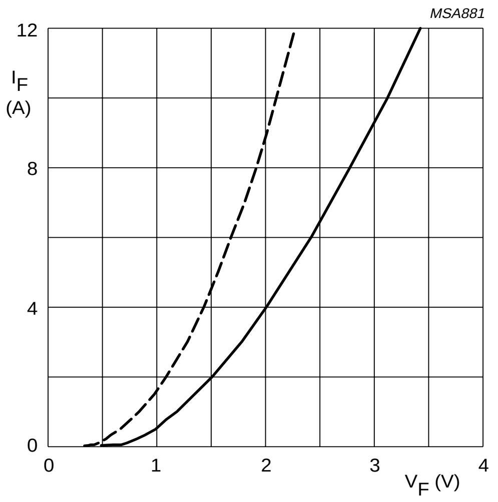


BYM36A to C

Dotted line: $T_j = 175$ °C.

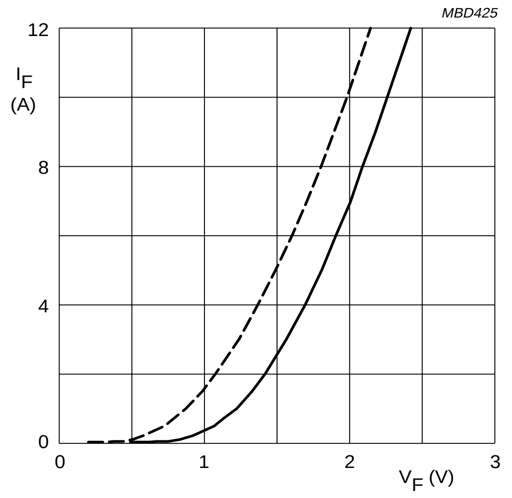
Solid line: $T_j = 25$ °C.

Fig.19 Forward current as a function of forward voltage; maximum values.



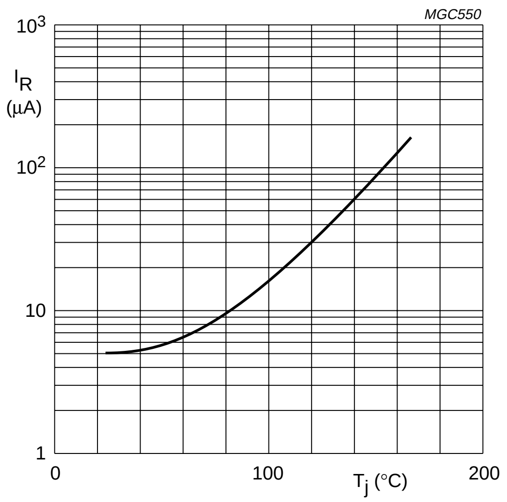
BYM36D and E.
Dotted line: T_j = 175 °C.
Solid line: T_j = 25 °C.

Fig.20 Forward current as a function of forward voltage; maximum values.



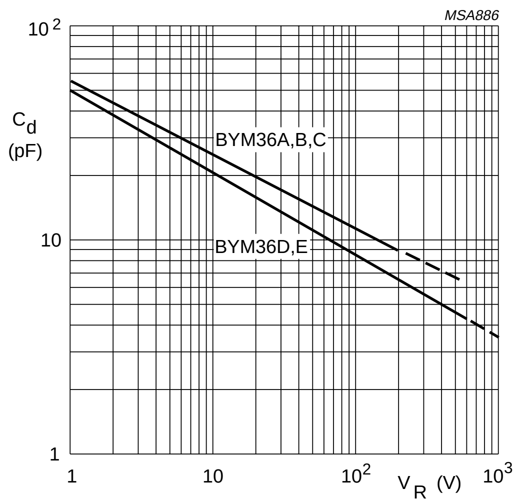
BYM36F and G.
Dotted line: T_j = 175 °C.
Solid line: T_j = 25 °C.

Fig.21 Forward current as a function of forward voltage; maximum values.



$V_R = V_{RRMmax}$.

Fig.22 Reverse current as a function of junction temperature; maximum values.



BYM36A to E
f = 1 MHz; T_j = 25 °C.

Fig.23 Diode capacitance as a function of reverse voltage, typical values.

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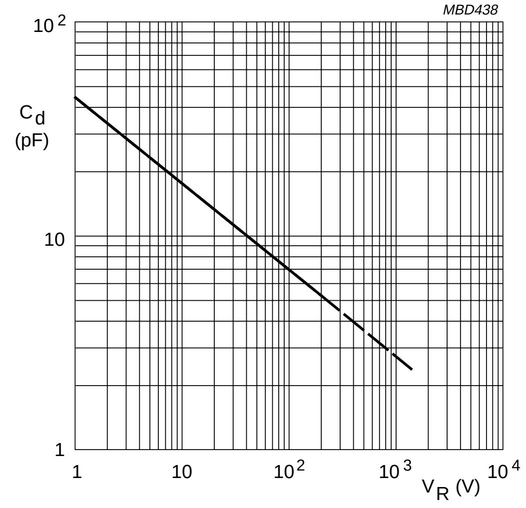
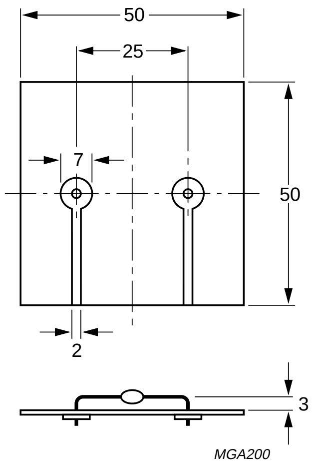


BYM36F and G

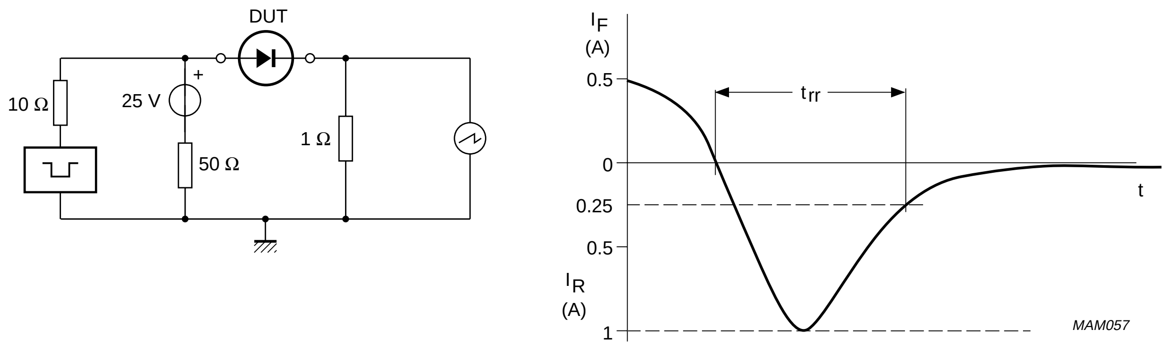
f = 1 MHz; T_j = 25 °C.

Fig.24 Diode capacitance as a function of reverse voltage, typical values.



Dimensions in mm.

Fig.25 Device mounted on a printed-circuit board.



Input impedance oscilloscope: 1 MΩ, 22 pF; t_r ≤< 7 ns.

Source impedance: 50 Ω; t_r ≤ 15 ns.

Fig.26 Test circuit and reverse recovery time waveform and definition.

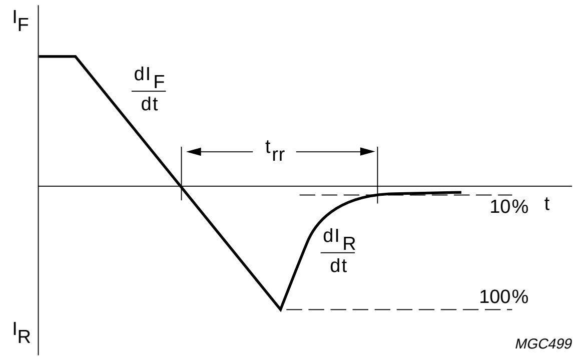


Fig.27 Reverse recovery definitions.

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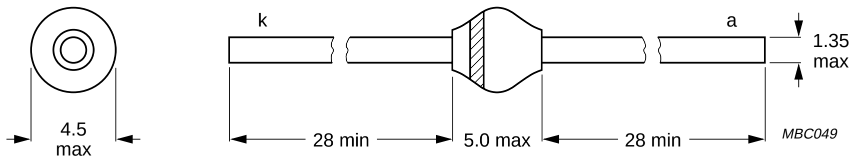
PACKAGE OUTLINE



Dimensions in mm.

The marking band indicates the cathode.

Fig.28 SOD64.

DEFINITIONS

Data Sheet Status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

LIFE SUPPORT APPLICATIONS

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